NSN 5962-01-373-9122

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∕laximum Poweı	Dissipation	Rating:
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1.04 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Sub hpa e/i fscm 49956

Features Provided:

Electrostatic sensitive and monolithic and schottky and programmed and bipolar

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Bipolar metal-oxide semiconductor

Case Outline Source And Designator:

D-3 mil-m-38510

Current Rating Per Characteristic:

100.00 milliamperes reverse current, dc

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, memory, digital, schottky bipolar 32k prom, monolithic silicon

Voltage Rating And Type Per Characteristic:

-0.3 volts applied and 7.0 volts applied

Time Rating Per Chacteristic:

95.00 nanoseconds access

Memory Device Type:

Prom

Hybrid Technology Type:

Monolithic

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

Specification Data:

67268-8200801ja government standard

Purchase Description Identification:

49956-g395748-10

Departure From Cited Designator:

Altered by programming & marking

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Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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